

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
1	BRS	L1	1412	(etch\$3 or remov\$3 or expos\$3 or contact\$3) same (("silcon carbide" or SiC) and (copper or Cu))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:36			0
2	BRS	L2	435	(etch\$3 or remov\$3 or expos\$3 or contact\$3) with (("silcon carbide" or SiC) and (copper or Cu))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 14:38			0
3	BRS	L3	341	438/\$.ccls. and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:37			0
4	BRS	L4	150	438/\$.ccls. and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:36			0
5	BRS	L5	761	@pd<=20010813 and 1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:53			0
6	BRS	L6	77	438/\$.ccls. and 5	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:53			0
7	BRS	L7	192	@pd<=20010813 and 2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 14:39			0
8	BRS	L8	17	438/\$.ccls. and 7	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:31			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r D e f i n i t i o n	E r r o r s
9	BRS	L9	18	6 not "18"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:53			0
10	BRS	L10	60	6 not 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 10:53			0
11	BRS	L11	170	(etch\$3) with (("silcon carbide" or SiC) same ("low k" or dielectric or insulat%3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 14:39			0
12	BRS	L12	136	(etch\$3) with (("silcon carbide" or SiC) with ("low k" or dielectric or insulat%3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 14:40			0
13	BRS	L13	223	(etch\$3) same (("silcon carbide" or SiC) with ("low k" or dielectric or insulat%3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 14:39			0
14	BRS	L14	19	@pd<=20010813 and 12	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:31			0
15	BRS	L15	6	((etch\$3) with (("silcon carbide" or SiC) with ("low k" or dielectric or insulat%3))) same ((carbon tetrafluoride or "CF.sub.4" or "CHF.sub.3" or trifluormethane or "CH.sub.4" or methane or difluoromethane or "CH.sub.2 F.sub.2") and ("H.sub.2" or hydrogen or "NH.sub.3" or ammonia))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:10			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	C o m m e n t s	E r r o r s	E r r o r s
16	BRS	L16	21	((etch\$3) same (("silcon carbide" or SiC) same ("low k" or dielectric or insulat%3))) same ((carbon tetrafluoride or "CF.sub.4" or "CHF.sub.3" or trifluoromethane or "CH.sub.4" or methane or difluoromethane or "CH.sub.2 F.sub.2") and ("H.sub.2" or hydrogen or "NH.sub.3" or ammonia))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:28			0
17	BRS	L17	664	((etch\$3) same ("silcon carbide" or SiC) same ((carbon tetrafluoride or "CF.sub.4" or "CHF.sub.3" or trifluoromethane or "CH.sub.4" or methane or difluoromethane or "CH.sub.2 F.sub.2") and ("H.sub.2" or hydrogen or "NH.sub.3" or ammonia))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:30			0
18	BRS	L18	165	((etch\$3) with ("silcon carbide" or SiC) with ((carbon tetrafluoride or "CF.sub.4" or "CHF.sub.3" or trifluoromethane or "CH.sub.4" or methane or difluoromethane or "CH.sub.2 F.sub.2") and ("H.sub.2" or hydrogen or "NH.sub.3" or ammonia))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:30			0
19	BRS	L19	101	@pd<=20010813 and 18	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:31			0
20	BRS	L20	31	438/\$.ccls. and 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/10 15:31			0